5/196/61/000/011/020/042 E194/E155 Differential phase protection of collector busbars Gasviani, B.I., and Dolidze, G.F. PERIODICAL, Referativnyy zhurnal, Elektrotekhnika i energetika, (Elektrotekhnika i energetika, 43-44 abstract llF. 308. Referationly Znurnal, Elektroteknnika i energet no.11, 1961, 43-44, abstract lie 308. (Elektroteknnika stantsii, no.4, 1961, 75-83) AUTHORS : The article describes a differential phase protection The article describes a differential phase protection with current-balance relays in which, unlike ordinary differential protection the starting devices check both the phase and the TITLE : with current-balance relays in which, unlike ordinary different protection, the starting devices check both the phase and the gralue of the differential current. protection, the starting devices check both the phase and the value of the differential current. The operating principles of this method of differential protection of collector bushars are this method of differential protection of collector busbars are considered, together with the questions of the starting considered, together with the questions of selection and calculation of the phase characteristics of the starting devices and their construction the circuit for selection the demonstruction calculation of the phase characteristics of the starting device and their construction, the circuit for selecting the damaged gystem of hughers and the use of combined filters for symmetric system of busbars and the use of combined filters for symmetrical components of currents. A simplified diagram is given of a components of currents. A simplified diagram is given of a device differential phase protection of busbars having a starting device with normally open contacts. differential-phase protection of busbars having a starting device with normally-open contacts, the characteristics of the starting card 1/4

Differential phase protection of ...

S/196/61/000/011/020/042 E194/E155

device in a complex plane, the phase characteristics of the starting device, vector diagrams for cases of external shortcircuit and short-circuit on the busbars, a schematic diagram of the differential phase protection with starting device having normally closed contacts, curves to determine the location of the centre of the required characteristics as function of the magnitude of the negative error of the current transformer and filter, curves to determine the possibility of executing differential phase protection with appropriate circuits, a a hemati: diagram for selection of faulty busbar system, a diagram of combined current filter and diagram of location of starter device windings and distribution of fluxes in the relay magnetic system. The introduction and operation of differential phase protection is described. A protective system is considered that uses the differential phase principle but is of higher sensitivity than ordinary differential protection circuits and does not react to large out-of-balance currents, so that it cam be used in a circuit with current transformers of high error. In selecting and calculating the phase characteristics of the Card 2/4

Differential phase protection of ... S/196/61/000/011/020/042 E194/E155

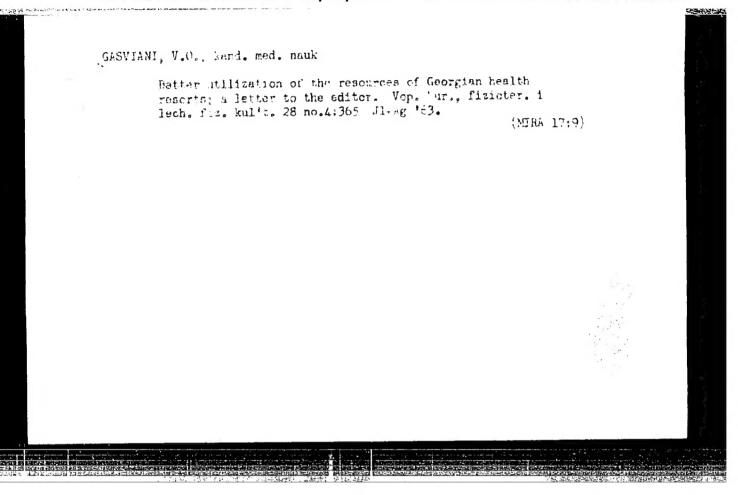
starting device it is assumed for simplicity that during external short-circuits only the current transformers and filters through which the total external short-circuit current flows give rise to error in transformation of the primary current and that there is no transformation error during short-circuits on the busbars. Here the maximum error of angle is 35° and of current +15%. With differential phase protection on current transformers of different transformation ratios the secondary currents are equalised by altering the number of turns of the primary winding of the combined symmetrical-component current filters. Winding data of suitable filters are given. It is stated that for reasons of economy the filter cables are located not on the busbar protective panels but at the places where the current circuits run, for instance, in switchgear drives, on control panels, etc. A disadvantage of the differential phase protection considered is that it requires the use of non-standard relays and current filters. Therefore, this type of protection is recommended only in cases where ordinary differential phase protection is insufficiently sensitive and selective. Differential phase protection may be based on a

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Differential phase protection of ... S/196/61/000/011/020/042 E194/E155

simpler circuit of incomplete differential phase protection if some of the elements connected to the collector busbars have current transformers with errors that permit the use of normal differential phase protection. The construction of starter devices and selection of their phase characteristics is carried out in the same way as with complete differential phase protection.

[Abstractor's note: Complete translation]



HIKITE, V.S., kand. tekhn. nauk; CASKIE., ...A., inzh.

Study of the dustines; of air near stone cutters in quarries.
Bor'ba s sil. 6:123-129 '64. (*IRA 18:2)

1. Institut gernege dela in. A.A. Skochinskogo.

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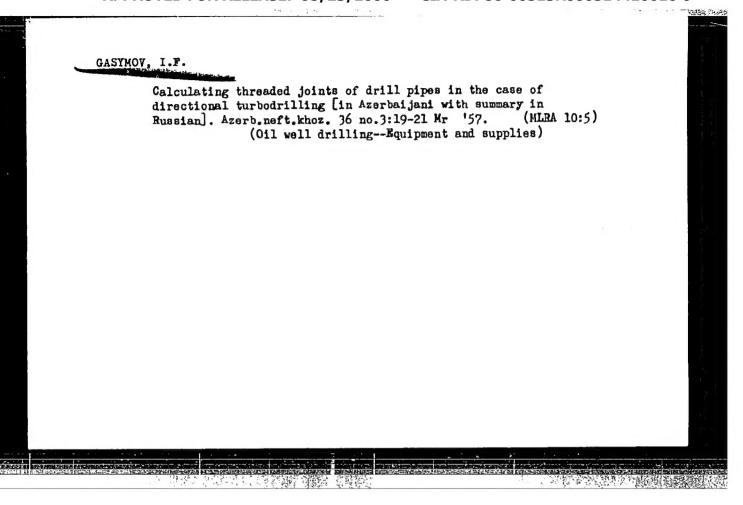
Sominkling during the operation of stoneoutting machines in quarries.

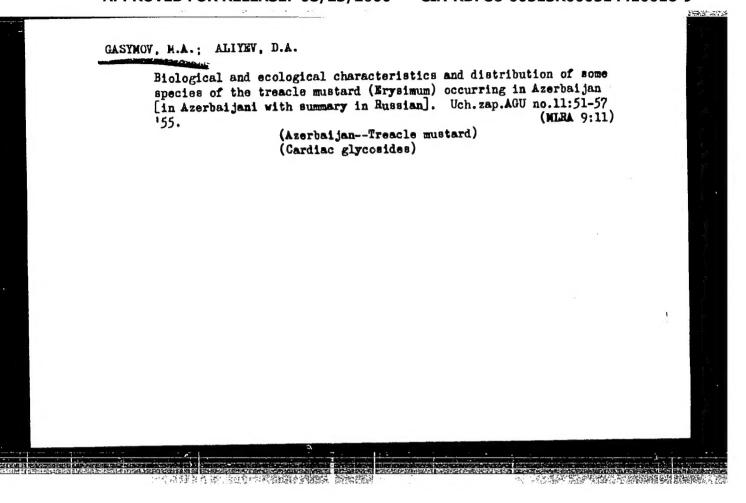
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1. Institut gornogo dela imeni Skochinskogo.

(MIRA 18:5)

CIA-RDP86-00513R000514410016-9





L 12664-63 EWT(d)/FCC(w)/BDS IJP(C) ACCESSION NR: AP3002862 T8/9020/63/150/005/0971/0974 AUTHOR: Gasy mov, M. G. TITLE: Analytic properties of a spectral function of a self-adjoint Sturm-Liouvil operator 16 SOURCE: AN SSSR. Doklady*, v. 150, no. 5, 1963, 971-974 TOPIC TAGS: Sturm-Liouville operator, Cauchy problem . ABSTRACT: Some results are stated on the analytic behavior of the spectral function of the operator originating from the differential equation (1) of the Enclosure. With the aid of these results, the author obtains asymptotes of the solution of the Cauchy problem (2) of the Enclosure. "The author expresses his sincere gratitude to his mentor F. A. Levitan for criticism of results." Orig. art. has: 15 formulas. ASSOCIATION: , none SUBMITTED: 10Jan63 DATE ACQ: 15Jul63 SUB CODE: NO REF SOV: Card 1/2/

GASYMOV, M.G.

Sum of differences of the eigenvalues of two self-adjoint operators.
Dokl. AN SSSR 150 no.6:1202-1205 Je '63. (MIRA 16:8)

1. Predstavleno akademikom A.A.Dorodnitsynym.
(Operators (Mathematics))

L 15472-63 EWT(d)/FCC(w)/BDS . AFFTC/LIP(C)
ACCESSION NR: AP3005425 S/0020/63/ 151/005/1014/1017

AUTHORS: Gasy*mov, M. G.; Levitan, B. M.

TITLE: Sum of the differences of the eigenvalues of two singular Sturm-Liouville operators 16

SOURCE: AN SSSR. Doklady*, v. 151, no. 5, 1963, 1014-1017

TOPIC TAGS: eigenvalue, difference sum, perturbation, Sturm-Liouville operator, boundary condition

ABSTRACT: This is a continuation of a study carried out by M. G. Gasy*mov (DAN, no. 5, 1963, p. 150) wherein a formula was proposed for the case of two singular Sturm-Liouville operators with discrete spectra differing from each other only by finite perturbation. Authors studied the sum of the differences of the Eigenvalues of two singular Sturm-Liouville operators which differed from each other by boundary conditions and finite perturbation. An analogue for Gasy*-mov's formulas was obtained and some necessary conditions were proven so that the two sequences of numbers and were eigenvalues of one singular

Sturm-Liouville equation but with different boundary conditions. Three theorems are Card 1/2, proved. Orig. art. has: 23 formulas.

s/0042/64/019/002/0003/0063

ACCESSION NR: AP4031754

AUTHORS: Levitan, B. M.; Gasykmov, M. G.

TITLE: Determination of a differential equation from two spectra .

SOURCE: Uspekhi matematicheskikh nauk, v. 19, no. 2, 1964, 3-63

TOPIC TAGS: differential equation, spectral function, differential equation determination, differential operator, linear integral equation, Parseval equality, Sturm Liouville equation, asymptotic formula, Sturm Liouville operator

ABSTRACT: Section titles are:

I. Determination of a differential equation from its spectral function

1. On the spectral function of a differential operator

2. Derivation of a linear integral equation for the kernel K(x,t) 3. Inverse problem. Solvability of the integral equation for the kernel K(x,t)

4. Derivation of the differential equation

5. Parseval equality

Classic Sturm-Liouville problem

Card 1/5

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Tions 110 on the	n from two spectra
II. Determination of a regular Sturm-Liouville equation	he spectrum
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- I Lotio formillas IOF the number on	
5 Torrowco Sturmeliouville Production	
III. Determination of the singular Sturm-Liouville pro	blem from two spectra urm-Liouville operators for
various boundary conditions $\alpha_n(h_1)$ in terms of the	spectrum
3. One class of potentials problem for the class Ω 1	
he Solution of the inverse products	
Application I. Proof of a theorem of V. A. Ambartsumys Application II. Derivation of asymptotic formulas (1.6	an 6.6) and (1.6.7)
Given two sequences of real numbers λ_0 , $\lambda_1,\ldots,\lambda_n$,	; μ_0 , μ_1 ,, μ_n ,
the authors treat the problem of finding necessary the	le operator of the form
$[y' + (\lambda - q(x))] y = 0 \qquad (0 < x < b < \infty$); (1) <u> </u>
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nde n e	various boundary conditions. Here $q(x)$ is a real function which is summable that interval $(0,b^{\dagger})$, $b^{\dagger} < b$. In the first section the authors find a solution that interval $(0,b^{\dagger})$, $b^{\dagger} < b$. In the first section the authors find a solution that is a section of the spectral function, based on the
01]	wing: Let $\rho(\lambda)$ be the spectral function of the problem $y' + (\lambda - q(x))y = 0$, $0 < x < \infty$; (2)
	y + (x - y/2)/3
	y(0)=1, $y'(0)=n$, $y'(0)=n$, and h is $q(x)$ is a real function having local symmetry of arbitrary order m, and h is
he:	1 number. Set $\varrho(\lambda) = \begin{cases} \varrho(\lambda), & \lambda \leq 0 \\ \varrho(\lambda) - \frac{2}{\pi} \sqrt{\lambda}, & \lambda > 0. \end{cases}$
	as $N \to \infty$, the integral $\int_{-\infty}^{N} \cos \sqrt{\lambda} x d\sigma(\lambda) \tag{5}$
	erges uniformly in each finite interval $(0 \le x \le b \le \infty)$ to the function (x)
whi tio	has an (m+1) st locally summable derivative. The authors find a new presenta- of the solution of the inverse problem from the spectral function for the case of the solution of the inverse problem from the spectral function for the case of the solution of the basic problem for the case of a regular Sturm-Liouville solution of the basic problem for the case of a regular Sturm-Liouville

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	wing formula is bas $\alpha_n = h_1 - \frac{h_2 - \frac{h_1 - \frac{h_2 - h_2 - h_2 - h_2 - \frac{h_2 - \frac{h_2 - h_2 $	$\frac{\lambda_n}{\lambda_n} \prod \frac{\lambda_k - \lambda_n}{\mu_k - \lambda_n}$;	(6)
0 1 .0 3 1	s spectra. Formula om two spectra. Kno	of a regular Sturm-Liou (6) gives a conditional wing the numbers $\{\lambda_n\}$	00200
the formula		$\varrho(\lambda) = \sum_{\lambda_{m} < \lambda} \frac{T_{n}}{\alpha_{n}}$	(7)
prescription. Obtaind sufficient con	aining an asymptotic ditions for the two	I reduce the operator acces expansion for α_n , the sequences of real number	ording to the previous y find necessary $x \in \{A_n\}$ and $\{\mu_n\}$ to
be two spectra of	one and the same equivalent $y'' + (\lambda - q(x))$	$y=0 \qquad (0 < x < \pi);$	(8)
article. In the t	\sim) $(0 < x < \pi)$	i.e., they solve the basi thors study the inverse p	c problem of the problem for the
operator Card 4/5	• 31		

ACCESSION NR: AP4031754 $y'' + \{\lambda - q(x)\} y = 0 \qquad (0 < x < \infty), \tag{9}$

y'(0) - hy(0) = 0, (10)

where q(x) is a real locally summable function and h is a real number. At the end of this section they find an unconditional solution of the inverse problem (from two spectra) for one class of potentials. Orig. art. has: 292 formulas.

ASSOCIATION: none

SUBMITTED: 08Jul63 DATE ACQ: 30Apr64 ENCL: 00

SUB CODE: MA NO REF SOV: 029 , OTHER: 006

Card 5/5



ACCESSION NR: AP403031.7

5/0249/64/020/001/0003/0008

AUTHOR: Gasy*mov, M. G.

TITLE: Applications of an inequality for the sum of difference of eigenvalues of two self-adjoint operators

SOURCE: AN AzerbSSR. Doklady*, v. 20, no. 1, 1964, 3-8

TOPIC TAGS: difference of eigenvalues, self-adjoint operator, Hilbert space, operator bounded from below, discrete spectrum, eigenvalue, orthonormalized eigen elements

ABSTRACT: In a previous paper ("DAN SSSR" (v pechati)), the author obtained the inequalities $\sum_{n=1}^{N} (\omega(B)\psi_{n}, \psi_{n}) \leqslant \sum_{n=1}^{N} [\omega(\mu_{n}) - \omega(\lambda_{n})] \leqslant \sum_{n=1}^{N} (\omega(B)\psi_{n}, \psi_{n}), \tag{1}$

where the operator $\omega(B) = \omega(c) = \omega(A)$, $\omega(t)$ is a continuous nondecreasing function, where A and C are self-adjoint operators, bounded from below, in a Hilbert space H, and having identical domain of definition D and discrete spectra. Card 1/2

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ACCESSION NR: AP4030347		
normalized eigen element and indicates their appl of the known theorem of for approximate computat	ad $\mathcal{H}_1 \subseteq \mathcal{H}_2 \subseteq \cdots$ be the eigenvalues of \mathcal{H}_1 , \mathcal{H}_2 , their is. The author obtains a generalization ications. With the help of (1) he obtains a most summer, and for certain cases he ion of the eigenvalues of the operator operator A. Orig. art. has: 16 forms	respective ortho- of inequalities (1) ins a generalization proposes a method
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GASYMOV, M.G.; LEVITAN, B.M.

Asymptotic behavior of the spectral function of a Schrödinger operator near a plane piece of the boundary. Izv. AN SSSR. Ser. mat. 28 no.3:527-552 My-Je 164. (MIRA 17:6)

GASYMOU, M.G.; LEVITAN, B.M. (Moskva)

Sturm - Louiville differential operators with discrete apectrum.

Mat. sbor. 63 no.3:445-458 Mr '64.

MIRA 17:4)

ACCESSION NR: AP4012072

3/0020/64/154/002/0254/0257

AUTHOR: Gasy*mov, M. G.

TITLE: Inverse problem for the Sturm-Liouville equation

SOURCE: AN SSSR. Doklady*, v. 154, no. 2, 1964, 254-257

TOPIC TAGS: mathematical analysis, differential equation, Sturm-Liouville equation, spectral function, summable derivative, local summable derivative

ABSTRACT: The differential equation

$$(1)$$

with boundary conditions y'(0) - hy(0) = 0. (2)

was examined. In this case, q(x) is a real, locally integrable function of x and h is a real number. Suppose that the function q(x) is such that any self-conjugate expansion of equation (1) has a discrete spectrum. The eigenvalues of the boundary value problem (1) - (2) are then denoted by $(\lambda_n(k))$, numbered in the order of increase,

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ACCESSION NR: AP4012072

and the orthonormal eigenfunctions corresponding to them by $\{ \varphi_n(\mathbf{x}, \mathbf{h}) \}$. Assuming that $h = h_1$ and $h = h_2$, where $h_1 \neq h_2$, we shall obtain two distinct boundary value problems with the eigenvalues $\{\lambda_n(\mathbf{h})\}$ and $\{\lambda_n(\mathbf{h}_2)\}$. Equation (1) is determined uniquely by the two spectra $\{\lambda_n(\mathbf{h}_2)\}$ and $\{\lambda_n(\mathbf{h}_2)\}$, but it is not known when the sequences of the alternate numbers $\{\lambda_n(\mathbf{h}_2)\}$ and $\{\lambda_n(\mathbf{h}_2)\}$ are eigenvalues of one and the same equation of type (1). Present work is devoted to the solution of this problem for one class of operators. The boundary value problem (1) - (2) was examined for $h = h_1$ and $h = h_2$, where $h_1 \neq h_2$. It is not difficult to show that

 $\int \varphi_n(x, h_1) \varphi_n(x, h_2) dx \left[\lambda_n(h_2) - \lambda_n(h_1) \right] = (h_2 - h_1) \varphi_n(0, h_1) \varphi_n(0, h_2).$

With $h_1 \rightarrow h_2 = h$, we obtain

(A)

The final formula is then

 $\lambda_n(h_1) - \lambda_n(h_1) = \gamma_n(0, h) dh.$

(5)

The spectral function of the problem (1) - (2) is then denoted by

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ACCESSION NR: AP4012072

 $\rho_a(N)$ and introduced into an examination of the function

$$\sigma_{l}(\lambda) = \frac{1}{h_{0} - h_{1}} \sum_{\lambda_{n}(h_{l}) \leq \lambda} \left(\lambda_{n} \left(h_{1} \right) - \lambda_{n} \left(h_{1} \right) \right), \quad l = 1, 2. \tag{6}$$

The final form of this function is

$$\rho_{h_0}(\lambda) = \sigma_1(\lambda) + \frac{h_0 - h_1}{2} + \frac{(h_0 - h_1)^n - 3(h_0^n - h_1^n)}{3\pi \sqrt{\lambda}} + O\left(\frac{1}{\lambda^{1/s + h_0}}\right)^{\frac{1}{2}}$$
(7)

where $\delta_{a}>0$. The function ρ_{a} has all of the properties of the spectral function of the Sturm-Liouville operator, and the potential $q(x) \in \Omega$ can be set up by this formula. "Author wishes to thank Prof. B. M. Levitan for his help during this study". Orig. art. has: 20 equations.

ASSOCIATION: Akademiya nauk SSSR (Academy of Sciences SSSR)

SUBMITTED: 20May63

DATE ACQ: 14Feb64

ENCL: 00

SUB CODE: MM

NR REF SOV: 007

OTHER: 000

Card 3/3

GASYMOV, M.G.

Expansion in eigenfunctions of a non-self-adjoint boundary value problem for a differential equation with a singularity at zero. Dokl. AN SSSR 165 no.2:261-264 N 165.

(MIRA 18:11)

1. Moskovskiy fiziko-tekhnicheskiy institut. Submitted April 5, 1965.

ACCESSION HR: AUTHOR: Gesyments TITLE: Determine the sequent on the sequent equation definition of a sin were known to for such case ASSOCIATION:	ination of the Sturm-Liquiville equation, no. 2, 1965, differential equation, spectrum, execution ces $\{\lambda_n\}$ and $\{\mu_n\}$ such that the ned on $\{0,\pi\}$ with a singularity positive integer. This result appular equation from two sets λ_0 be spectra. He first solves the	274-276 igenvalue of the problem of finding conditions ey be two distinct spectra of one at π of the type $\ell(\ell+1)/(\pi-x)^2$ uplies to the constructions previously $\ell > 1 < \dots $ and $\ell < \ell < \ell < \dots $ which usual inverse Sturm-Liouville problem institut (Yoscow Physico-Technical	
Institute) SUBMITTED: NO REF SOV: Card 1/1	16Sep64 ENCL: 00	SUB CODE: MA	

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1.1	C 37076-66 FWT(d)/EWP(1) 1.F(c) SOURCE CODE: TR/CO20/66/167/005/0967/0970	<u> </u>
-	AUTHORS: Gasymov, M. G.; Levitan, B. M.	2
	ORG: Moscow State University im. M. V. Lomonosov (Moskovskiy gosudaretvennyy universitet)	10 to
	TITLE: The inverse problem for a Dirac system	
	Doklady, v. 167, no. 5, 1966, 967-970	
	TOPIC TAGS: Dirac system, Dirac problem, spectral function, differential equation, orthogonal transformation	
	ABSTRACT: The system of Dirac differential equations $(B d/dx + Q(x)) y = \lambda y, 0 \le x < \infty$	
	is studied, where $B = \begin{pmatrix} 0 & 1 \\ -1 & 0 \end{pmatrix}, \ Q(x) = \begin{pmatrix} p(x) & q(x) \\ q(x) & r(x) \end{pmatrix}, \ y = \begin{pmatrix} y_1 \\ y_2 \end{pmatrix}.$	
	Here it is supposed that p, q, and r are real functions which are integrable from $(0,\infty)$. The solution of this equation is designated by $\varphi(x,\lambda) = \begin{pmatrix} \varphi_1(x,\lambda) \\ \varphi_2(x,\lambda) \end{pmatrix},$	
	with the initial conditions $\varphi_1(0,\lambda) = \sin \alpha, \varphi_2(0,\lambda) = -\cos \alpha$	
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ACC NR: AP6012910

where a is a real number. Additional system conditions are

$$f(x) = \binom{f_1(x)}{f_1(x)} \in L_1(0, \infty) ,$$

$$f(x) = \binom{f_1(x)}{f_2(x)} \in L_1(0, \infty) ,$$

$$F_n(\lambda) = \int_0^n \{f_1(x) \varphi_1(x, \lambda) + f_2(x) \varphi_2(x, \lambda)\} dx.$$

For each matrix Q(x) and each number α it can be shown that there exists a unique nondiminishing function $P(\lambda)$ such that

$$\int_{0}^{\infty} \left(f_{1}^{2}(x) + f_{2}^{2}(x)\right) dx = \lim_{n \to \infty} \int_{-\infty}^{\infty} F_{n}^{2}(\lambda) d\rho(\lambda).$$

The authors prove the necessary and sufficient conditions for the function $P(\lambda)$ to be the spectral function of the given Dirac equation system. A single-valued definition of this system is sought in terms of the spectral function. The approach taken is one of reducing the system to a canonical form by which the single-valued definition can be determined through $\rho(\lambda)$. It is shown that this prototype system can be reduced to canonical form by means of an orthogonal transform. Four theorems are stated in demonstrating the veracity of the approach. This paper was presented by Academician A. A. Dorodnitsyn on 16 July 1965. Orig. art. has: 10 equations.

SUB CODE: 12/ SUBM DATE: 14Jul65/ ORIG REF: 002/ OTH REF: 003

ENT(d)/SNP(1) IdP(c) L 43143-66 SOURCE CODE: UR/0020/66/167/006/1219/1222 ACC NR: AP6013887 AUTHOR: Gasymov, M. G.; Levitan, B. M. ORG: Moscow State University im. M. V. Lomonosov (Moskovskiy gosudarstvennyy universitet) TITLE: Determination of the Dirac system in terms of scattering phase SOURCE: AN SSSR. Doklady, v. 167, no. 6, 1966, 1219-1222 TOPIC TAGS: boundary value problem, continuous spectrum, equation solution, NVERSE PROBLEM ABSTRACT: A solution is given to the inverse problem of scattering theory for the Dirac system of equations. The solution is based on a canonical form of the Dirac system of equations previously stated by the authors (DAN, 167, No. 5, 1966). The transfer operator stipulated at infinity is of fundamental importance to the solution. It is noted that the inverse problem with respect to the given scattering for the Dirac system in the case where its coefficients have the characteristic of form (0 - 1/x) at zero and infinity cannot be solved in this way. It is demonstrated that the scattering data of the problem without a characteristic are the scattering data of the problem with a characteristic of the indicated type and vice versa. The paper was presented by Academician Dorodnitsyn, A. A., 16 July 65. Orig. art. has: 21 formulas.

SUB CODE: 12/ SUBM DATE: 14Jul65/ ORIG REF: 002/ OTH REF: 003

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UDC: 517.948.35

CIA-RDP86-00513R000514410016-9

SOURCE CODE: UR/0020/66/169/005/1037/1040 IJP(c)______ MAT(d) L 10086-67 ACC NAI APOO30008 AUTHOR: Gasymov, M. G. TITLE: The inverse scattering problem in terms of data for a system of dirac equations SOURCE: AN SSSR. Doklady, v. 169, no. 5, 1966, 1037-1040 TOPIC TAGS: scattering matrix, eigenvalue, asymptotic property ABSTRACT: The inverse scattering problem' is solved for the system of equations $B_n y' + mC_n y + Q(x) y = \lambda y, \quad 0 \le x < \infty,$ $B_n = \begin{pmatrix} 0 & I_n \\ -I_n & 0 \end{pmatrix}, \quad I_n = \begin{pmatrix} 0 \dots 0 & 1 \\ 0 \dots 1 & 0 \\ \vdots & \vdots & \vdots \\ 1 \dots 0 & 0 \end{pmatrix}, \quad C_n = \begin{pmatrix} E_n & 0 \\ 0 & -E_n \end{pmatrix},$ where Here I_n and E_n are matrices of order n, E_n being the unit matrix; Q(x) is a hermitian matrix function of order 2n, y is a column vector with 2n components and m is a constant. This problem is a generalization of previous work done for n = 1. The canonic-Card 1/3

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al form of this system of dirac equations is used, i. e., where

$$Q(x) = \begin{pmatrix} P & \Omega \\ \Omega^{\bullet} & -P \end{pmatrix}, \qquad (2)$$

where P and Ω are matrices of order n; P is hermitian and Ω is symmetric with respect to the second diagonal. Further, P(x) and Q(x) are restricted such that for every xin [0, -]

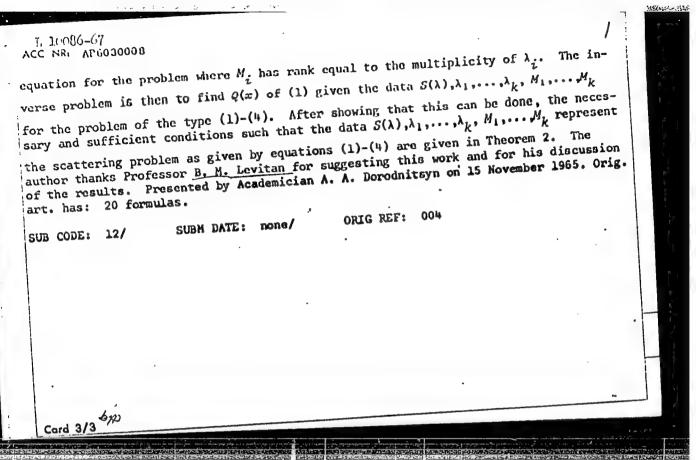
 $||P(x)|| \le C/(1+x)^{\frac{1}{1+\epsilon}}, \quad ||Q(x)|| \le C/(1+x)^{2+\epsilon},$

where c and ϵ are constants greater than zero. The unique form for the 2nth order matrix solution $f(x,\lambda)$ of the equations (1)-(3) for every λ with Im $\lambda > 0$ is given by Theorem 1. Using this, the exact form of the scattering problem is given for the bound- $\tilde{y}_1(0) = \ldots = y_n(0) = 0,$ (4) ary conditions

where y_1, \dots, y_n are the first n components of the vector function y(x). The problem given by equations (1)-(4) has a finite number of discrete eigenvalues $\lambda_1, \dots, \lambda_k$ from (-m,m) which coincide with the roots of the determinant of $f_1(0,\lambda)$ where $f_1(0,\lambda)$ is the matrix corresponding to the first n rows of the matrix $f(0,\lambda)$. The scattering problem is completely specified when one includes, in addition to the λ_i 's, the unitary scattering matrix $S(\lambda)$ which defines the asymptotic behavior of the eigenfunctions and the positive definite matrices M_1, \dots, M_k which are determined by the Parseval

Card 2/3

CIA-RDP86-00513R000514410016-9



CIA-RDP86-00513R000514410016-9

ACC NR: AP7011825

SOURCE CODE: UR/0249/66/022/010/0009/0012

AUTHOR: Gasymov, M. C.

ORG: MGU

TITLE: Analysis of the solution to a problem in scattering theory for a non-self-adjoint Schrodinger equation

SOURCE: AN AzerbSSR. Doklady, v. 22, no. 10, 1966, 9-12

TOPIC TAGS: mathematic space, Schroedinger equation

SUB CODE: 12,20

ABSTRACT: The article concerns the completeness of solutions to a problem in scattering theory for the case of a non-selfadjoint Schrodinger equation defined in an entire space. The author considers the equation

$$-\left\{\frac{\partial^2 u}{\partial x_1^2} + \frac{\partial^2 u}{\partial x_2^2} + \frac{\partial^2 u}{\partial x_3^2}\right\} + q(x_1, x_2, x_3)u = \lambda^2 u , \qquad (1)$$

with the assumption that the complex-valued function $q(x_1, x_2, x_3) = q(x)$ is defined in the entire space E_3 and satisfies the inequality

Card 1/2

1933

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ACC NR: AP7011825

$$|q(x)| \leqslant Ce^{-\alpha r}$$

C and ϵ are constant positive numbers, $r=(x_1^2+x_2^2+x_3^2)^{\frac{1}{2}}$.

Letting w equal a unit vector in E3 he shows that the solution of the equation

is a solution of the problem in scattering theory for equation (1).

$$u(x; \lambda, \bullet) = e^{i\lambda(x, \bullet)} + \int \frac{e^{i\lambda(x-y)}}{|x-y|} q(y) u(y; \lambda, \bullet) d^3y$$

This article was presented by Academician AN AzerbSSR Z. I. Khalilov. Orig. art. has: 23 formulas. JPRS: 40,393

Card 2/2

ABDULLAYEV, C.B.; BAKIROV, M.Ya.; GASYMOV, R.B.; NASIROV, Ya.N.

Investigating the formation of a p-n junction in selenium photocells. Part 1: Effect of the material of the top electrode. Izv. AN Azerb. SSR. Ser.fiz.-mat. i tekh. nauk no.4:66-72 '60. (MRA 14:3)

(Photoelectric cells) (Selenium)

AEDULLAYEV, G.B.; GASYMOV, R.B.; BAKIROV, M.Ya; NASIROV, Ya.N.

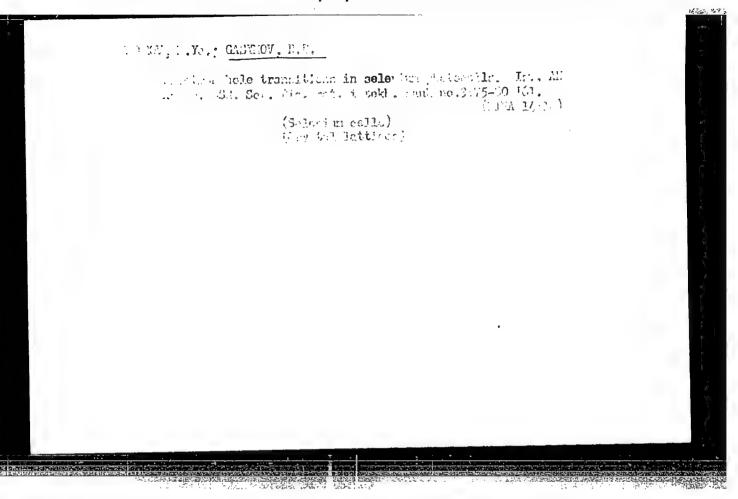
Heat-resistant selenium photocells. Izv.AM Azerb.SSR.Ser.fiz.mat.i tekh.nauk no.5:79-84 '60. (HIRA 14:4)

(Photoelectric cells) (Selenium)

ABDULLAYEV, G.B.; BAKIROV, M.Ya.; GASYMOV, R.B.; NASIROV, Ya.N.

Selenium photoelectric cells with layers of CdO, CdS, CdSe, and CdTe. Izv. AN Azerb. SSR. Ser. fiz.-mat. i tekh. nauk no.6: 77-83 '60.

(Photoelectric cells)



S/194/61/000/010/054/082 D256/D301

9,4160

26.1512 AUTHORS:

Abdullayev, G.B., Bakirov, M.Ya., Gasymov, R.B. and

Nasirov, Ya.N.

TITLE:

Selenium photo-cells with layers of CdO, CdS, CdSe

and CdTe

PERIODICAL:

Referativnyy zhurnal. Avtomatika i radioelektronika, no. 10, 1961, 28-29, abstract 10 G196 (Izv. AN AzerbSSR. Ser. fiz.-matem. i tekhn. n., 1960, no. 6,

TEXT:

Results are presented of investigations of n-type
selenium photo-cells with layers of CdO, CdS, CdSe and CdTe of high
selenium photo-cells with layers of the spectrum. The photo-effect
sensitivity in the visible region of the spectrum. sensitivity in the visible region of the spectrum. The photo-effect in these cells occurs due to p-n transitions at the borders Se-CdO, Se-CdS, Se-CdSe and Se-CdTe. In preparing the photo-cells the mat- visible control of the top electrode was of no significant importance and did not require special forming. not require special forming. The photo-current of the mentioned

Card 1/2

APPROVED FOR RELEASE: 08/23/2000

CIA-RDP86-00513R000514410016-9"

38366

S/058/62/000/005/095/119 9,4160 A061/A101

26.15/2

AUTHORS:

Bakirov, M. Ya., Gasymov, R. B.

TITLE:

p-n junction in selenium photoelectric cells

PERIODICAL: Referativnyy zhurmal, Fizika, no. 5. 1962, 36-37, abstract 5E289 ("Izv. AN AzerbSSR. Ser. fiz.-matem. i tekhn. n.", 1961, no. 3,

75-80. Azerb. summary)

The electrical and photoelectric characteristics of a selenium photoelectric cell with a p-n junction obtained by applying Cd to the surface of polycrystalline p-type Se have been investigated experimentally. In a diode circuit, at a voltage V of the order of kT/q, the dependence of the current I on V is linear. In the range 0.1 < V < 0.8 v, I = I₀ exp (qV/ β kT), I₀ = 4.6 · 10^{-7} a/cm^2 , and $\beta = 4.1$. At high voltages. Ohm's law is observed due to the effect of the resistance of the semiconductor material thickness. No saturation current is observed in the inverse direction. The dependence of the shortcircuit current on the no-load voltage under illumination is given by the same formula as applies also to the dark characteristic at 0.1 < V < 0.8 v; however,

Card 1/2

p-n junction in selenium photoelectric cells

S/058/62/000/005/095/119 A061/A101

 $\Gamma_0 = 1.5 \cdot 10^{-6}$ a/cm², and $\beta = 3$. The spectrum sensitivity has an absolute maximum at λ 0.56 μ , and an additional maximum at 0.71 μ . The half-life period of the spectrum sensitivity distribution corresponds to 0.63 μ . The maximum power output of the load, the optimum loading impedance, and the efficiency of the photoelectric cell fit the general theory. At a solar radiation of 100 mm/cm², the short-circuit current is 3 ma/cm², the no-load emf is 0.6 ν , and

Yu. Ravich

[Abstracter's note: Complete translation]

Card 2/2

ABBULIATEN, G.B.; GESPACOV, R.B.; ELETIN, E.No.

Sclenium; photocells with a Gade layer. Dokt. M. Azerb.

GSR 17 nc.F:477-680 '61.

1. Institut: Maiki M. Azerbish.

(Sclenium; cells)

(Gallium)

1,2038 \$/233/62/000/003/006/010 TO11/1211

AUTHORS:

Pakirov, M.Ya., Gasymov, R.B.

TITLE:

Selenium photoelements with a mercury selenide layer

PERIODICAL: Akademiya nauk Azerbaydzhanskoy SSR. Izvestiya. Seriya fiziko-matematicheskikh i tekhnicheskikh nauk, no.3,

1962, 89-94

TEXT: The specimens tested were made of: (1) technical p-type selenium with 10¹⁵ holes per cm³, mobility at room temperature of 0.052 cm² and forbidden band width of approximately 2eV; (2) n-type

vsec mercury selenide with 10^{17} electrons per cm³, mobility at room temperature of 90,000 cm², forbidden band width of 0.3eV. The mer-

cury selenide layer of approximately 1 A width was spread on the crystallised hexagonal selenium with an aluminium base by evaporation at 10-5 mm Hg vacuum. The HgSe used was obtained by synthesis. Cd was used for the upper electrode. It is seen from the volt-

Card 1/4

S/233/62/000/003/006/010

Selenium photoelements...

ampere characteristic that the cut-off voltage is 0.35V and the series internal resistance as determined by the linear section in the forward voltage branch is 18 ohms. The inverse current has no saturation. At voltages of the order of magnitude of $\frac{kT}{T}$ the forward and inverse characteristics are linear and the differential resistance at zero voltage, $R_0 = 10^4$ ohms. In the 0.1-0.5V forward voltage range the characteristic is given by

$$I_{f} = I_{o} \exp\left(\frac{qV_{f}}{\beta kT}\right),$$

$$I_{o} = 3x10^{-6} \frac{\Lambda}{cm^{2}}; \qquad \beta = 2.1$$
(1)

The wave length of the maximum spectral sensitivity of the investigated photoelements coincides with that of the common selenium ones - 0.56 m. There is a considerable increase in sensitivity in the investigated cells (some 20%) in the 0.8 - 1.4 m range. Photoele-

Card 2/4

S/233/62/000/003/006/010 I 011/I 211

Solonium photoelements ...

ments with an MgSe layer can be used in infra-red engineering. The short-circuit current depends linearly on the illumination in the 0-10⁴ lux range (a tungsten lamp with light temperature of 2840°K was used). The open circuit voltage first increases linearly with the illumination and then reaches saturation. The current of the carriers generated by the light and separated by the p-n junction field is given by

 $I_{f} = I_{o} \exp \frac{\text{qVoc}}{\hat{p}kT}$, (3) $I_{o} = 2.5 \times 10^{-6} \frac{\Lambda}{\text{cm}^{2}}$; $\hat{p} = 3.6$

and Voc is the open-circuit voltage. From here one gets

 $R_0 = \frac{3kT}{qL_0} = 3.4x10^4 \text{ ohms.}$

The reasons for the difference between the results as obtained from the volt-ampere diode characteristic and those obtained from the last relation are not clear. The temperature coefficient of

Card 3/4

S/233/62/000/003/006/010 I 011/1211

Selenium photoelements...

the open-circuit voltage is -2.7x10⁻³ V/degree in the HgSe layer photoelements and -1.1x10⁻³ V/degree in the common photoelements. The short-circuit current decreases with an increase in the temperature in the investigated specimens, while in common elements its decrease starts at 80°C. These results are true for 0-100°C range. There are 6 figures and 1 table. The most important English-language references read as follows: Lakschmann T.K. Proc. of the IRE, 9, 1646, 1960; Tubota H., Suzuki H.J. Phys. Soc. Japan, 14, No.1, 1959.

Card 4/4

S/058/62/000/005/051/136 A061/A101

9,4160

AUTHORS: Abdullayev, G. B., Gasymov, R. B., Bakirov, M. Ya.

TITLE: Selenium photocells with GaSe layer

PERIODICAL: Referativnyy zhurnal, Fizika, no. 6, 1962, 25, abstract 6G212 ("Dokl. AN AzerbSSR", 1961, v. 17, no. 8, 677 - 680, Azerb. summary)

TEXT: The photocells under consideration have been produced with a p-n junction formed on the contact of Se and GaSe. The presence of the latter was proved by electron diffraction. Apart from the principal maximum $(0.56\,\mu)$, these photocells display an additional maximum at $0.44\,\mu$, the relative magnitude of which depends on the thickness of metallic Ga applied to the Se film.

Ya. Oksman

[Abstracter's note: Complete translation]

Card 1/1

L 11047-63

EWT(1)/EWG(k)/BDS/EEC(b)-2

AFFTC/ASD/ESD-3

Pz-4 AT/IJP(C)

ACCESSION NR: AT3002972

S/2927/62/000/000/0005/0012

Q5 47

AUTHOR: Abdullayev, G. B.; Bakirov, M. Ya.; Gasy*mov, R. B.; Bakhy*shov, A. E.

TITLE: Investigating the nature of p-n junction in selenium photocells [Report at the All-Union Conference on Semiconductor Devices, Tashkent, 2-7 October 1961]

SOURCE: Elektronno-dy*rochny*ye perekhody* v poluprovodnikakh. Tashkent, Izd-vo AN UzSSR, 1962, 5-12

TOPIC TAGS: selenium photocell, p-n junction of photocell

ABSTRACT: Although selenium photocells have been widely used, many physical phenomena transpiring in them are not entirely clear. Experiments have shown that the junction is formed at the contact of two different semiconductors (e.g., Se and CdSe); the theory of such junctions has been developed. The article describes experimental studies of the p-n junction in and aging of selenium photocells. Also attempts to create a highly sensitive and stable photocell by coating Se with an electron-type semiconductor are reported. Photocurrent and photo-emf of Se coated with A1, Cu, Zn, Ga, Ag, Cd, In, Sn, Au, Hg, Pb, Bi were measured. Effects of thermal and electrical forming on the photocell characteristics were investigated.

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L 11047-63

ACCESSION NR: AT3002972

It was found that aging of selenium photocells is due to excessive thickening of the selenide coating (over the optimum thickness of 5 x 10 sup -5 cm). Four sets of artificial n-layer electrodes, Se-GaSe, Se-InSe, Se-GdSe, and Se-HgSe, were investigated in detail. Current-voltage, sensitivity spectral distribution, and illumination characteristics were determined for the above combinations (curves given), as well as all pertinent electrical and photoelectrical data (tabulated). With a solar-radiation intensity of 10 milliwatt per sq cm, current up to 3 ma per sq cm, and emf 0.6 v (efficiency about 1 per cent) were obtained for Se-CdSe combination. It is concluded that, in the selenium photocells, the p-n junction can be obtained by coating selenium with a thin layer of an electron-type semi-conductor. Orig. art. has: 5 figures, 5 formulas, and 1 table.

ASSOCIATION: Akad. nauk SSSR(Academy of Sciences SSSR); Akad nauk UzSSR(Academy of Sciences UzSSR); Tashkentskiy gosuniversitet im. V. I. Lenina (Tashkent State University)

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ENCL: 00

SUB CODE: 00

NO REF SOV: 010

OTHER: 003

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s/233/62/000/006/006/008 E010/E420

Abdullayev, G.B., Bakirov, M.Ya., Gasymov, R.B. AUTHORS:

A study of the effect of thickness of p- and n-layers TITLE:

on characteristics of selenium photocells

PERIODICAL: Akademiya nauk Azerbaydzhanskoy SSR. Seriya fiziko-

matematicheskikh i tekhnicheskikh nauk, no.6, 1962,

63-68

 Λ selenium photocell consists of a metallic backing, a TEXT: layer of polycrystalline selenium and an upper electrode. The thickness of semiconductors, such as selenium, is one of the main factors affecting characteristics of photocells. Selenium with a purity of 99.9999% was applied to an aluminum plate and ~0.1 µ thick cadmium layer served as the upper electrode. These photocells were subjected to illumination of 5000 lux intensity at at 20°C.perature. The generated photo-emf V and photocurrent I were measured. A linear growth of the series resistance R with increasing thickness of selenium layer is observed. Both photocmf and photocurrent values pass through a maximum at 50 µ thickness of selenium layer and then decrease. The effect of thickness of Card 1/2

A study of the effect ...

S/233/62/000/006/006/008 E010/E420

an n-layer on the efficiency of selenium photocells was also determined in order to study the nature of their ageing. A layer of n-type CdSe was applied to the surface of crystalline selenium. Measurements of the variation of photo-emf, V, and photocurrent, I, with thickness of the n-layer show that the optimum value of the latter is about 5 x 10-5 cm. Hence the nature of the ageing process of photocells is explained: the n-layer of CdSe increases with time on account of diffusion of Se into the Cd layer and this leads to the deepening of the p-n junction resulting in the reduced efficiency of the photocells. There are 5 figures.

Card. 2/2

ABDULLAYEV, G.B.; BAKIROV, M.Ya., GASYMOV, R.B.

Effect of the thickness of p and n-films on the characteristics of selenium photocells. Izv. AN Azerb. SSR. Ser. fiz.-mat. i tekh. nauk no.6:69-73 '62. (MIRA 16:6)

(Photoelectric cells) (Selenium)

ABDULLAYEV, G.B.; BAKIROV, M.Ya.; TALIBI, M.A.; GASIMOV, R.B.

Selenium photoelements with caturation current. Izv. AN
Azerb. SSR.Ser. fiz.-mat. i tekh. nauk no.3:77-83 '63.

(MIRA 16:11)

ACCESSION NR: AP4012599

s/0233/63/000/005/0069/0074

AUTHORS: Bakirov, M. Ya.; Gasy*mov, R.B.

TITLE: Investigating the relaxation processes in selenium cells with artificial P-N junctions

SOURCE: AN AzerbSSR. Izv. Ser. fiz.-matem. 1 tekhn. nauk, no. 5, 1963, 69-74

TOPIC TAGS: relaxation process , selenium cell, light intensity, photocurrent, P-N junction, barrier capacity, square pulse, inertness, recombination, current carrier, oscillograph

ABSTRACT: Selenium cells are used as receivers in most of the photometric instruments, as they can be used in conditions of rapidly changing illumination. But their shortcoming is a high degree of inertness. According to the theory (S.M. Ryvkin, Journal of Technical Physics, 27, 1676, 1957), the relaxation time in barrier conditions is determined either by the lifetime of the

Card 1/3

ACCESSION NR: AP4012599

minority carriers or the charging time of the barrier capacity. Cited in this project are the investigation results of the relaxation processes in photocells with CdO, CdS, CdSe, HgSe and GaSe layers. The investigation involved the use of the tau-metric method. Photo-emf is a function of the temperature, intensity and wavelength of the exciting light. A change in the temperature, intensity and wavelength of the exciting light therefore also changes the relaxation time. In selenium cells with artificial P-N junctions the inertness time depends on the N-layer material and lies in the range of 2.1-9.2 x 10-3 seconds. The inertness period diminishes with increasing light intensity, and increases with the increasing wavelength of the light. "The authors are grateful to A. Kh. Khalilov for his assistance in the measurements and discussion of the results." Orig. art. has: 5 figures, 1 formula and 3 tables.

ASSOCIATION: None

Card 2/3

ABDULLAYEV, G.B.; ALEKPEROVA, Sh.M.; TALIBI, M.A., BEKIROV, M.Ya.; GASYMOV. R.B.

Saturation currents in selenium p-n junctions. Dokl. AN Azerb. SSR 19 no.1:9-12 '63.

1. Institut fiziki AN AzSSR.

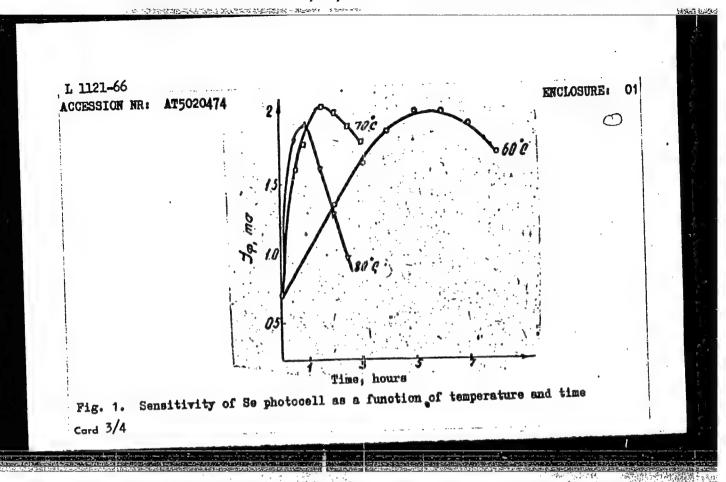
(Junction transistors)

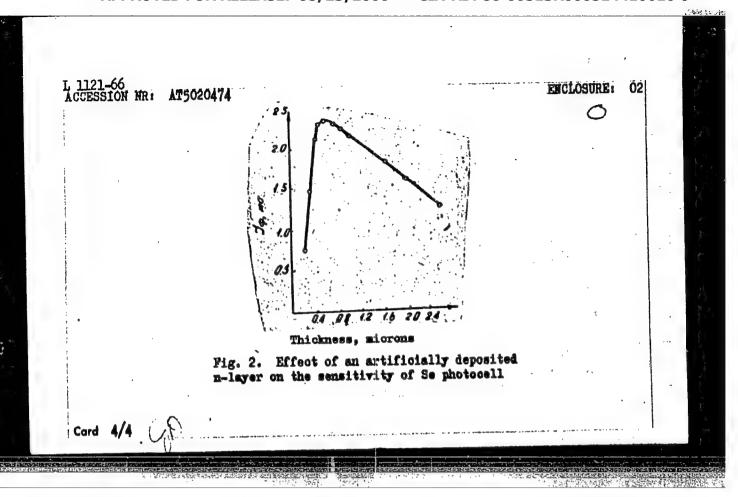
IJP(c) RDW/JD/GS ENT(m)/ETC/ENG(m)/ENP(t)/ENP(b) L 1121-66 UR/0000/64/000/000/0284/0289 AT5020474 ACCESSION NR: Abdullayev, G. B.; Bakirov, M. Ya.; Gasymov, R. B. 5.5 TITLE: Investigation of surface contact phenomena in selenium in contact with certain metals SOURCE: Mezhvuzovskaya nauchno-tekhnicheskaya konferentsiya po fizike poluprovodnikov (poverkhnostnyye i kontaktnyye yavleniya), Tomsk, 1962. III 155 Poverkhnostnyye i kontaktnyye yavleniya v poluprovodnikakh (Surface and contact phenomena in semiconductors). Tomsk, Izd-vo Tomskogo univ., 1964, 284-289 TOPIC TAGS: selenium, photocell, photo current, photodiode, photoconductive cell, group VI element, contact potential, cadmium, indium, mercury, gallium, lead, zino 27 27 27 ABSTRACT: The mechanism of the aging process in selenium photocells was studied. Cells made of Se and the netals Cd, In, Hg, Ga, Pb, and Zn were investigated. Electron-diffraction photographs of the binary contact between Se and the various metals showed it to consist of the selenides CdSe, InSe, HgSe, GaSe, PbSe and ZnSe. The sensitivity of photocells was determined as a function of the time and temperature and is shown graphically in Fig. 1 on the Enclosure. The effect of the depth of a deposited p-n junction on the response of Se photocell is shown in Fig. 2 on the Enclosure. It is concluded that the aging process consists of the growth of an Card 1/4

"APPROVED FOR RELEASE: 08/23/2000

CIA-RDP86-00513R000514410016-9

ACCESSION NR: AT5020474	photocell. Orig. art. has: 4 graph	s and 2 equations.
n-layer on the surface of the	a moscoure and	
	The state of the s	
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L 16505-66 EWT(1)/EWT(m)/ETC(f)/EWG(m)/EWP(t) IJP(c) RDW/JD/GS/AT ACC NR: AT6001334 SOURCE CODE: UR/0000/65/000/000/0085/0094 AUTHOR: Abdullayev, G. B.; Bakirov, M. Ya.; Talibi, M. A.; Gasymov, R. B. 66 ORG: none TITLE: Photoeffect in selenium pn transitions SOURCE: AN AzerbSSR. Institut fiziki. Selen, tellur i ikh primeneniye (Selenium, tellurium and their utilization). Baku, AN AzerbSSR, 1965, 85-94 TOPIC TAGS: selenium, intermetallic compound, impurity conductivity, semicondicting material, spectrum analysis, temperature dependence, diffusion coefficient, metal physics 21,44,55 ABSTRACT: Photoelectric properties of selenium photocells containing Cd, Pb, Ga, In, Zn and Hg as contact films were studied. Diffraction analysis of the junctions showed that the selenide intermetallic compound formed in each case; these junctions exhibited n-type conductivity and caused photovoltaic effects due to pn transitions. Spectral characteristics are given for Se with CdSe, InSe and HgSe, showing primary and secondary maxima for relative photocurrent (%), the secondary maximum being dependent on the type of element. Photosensitivity showed a dependence on time, sample 2 Card 1/2

L 16505-66

ACC NR: AT6001334

thickness and temperature. At constant temperature, the initial sensitivity rose, reached a maximum (about 2 ma) and then dropped sharply with time; the sharpest changes occurred at the higher temperatures. This held true for different thicknesses: the maximum was at 0.5µ. The thickness of the n-type layer was expressed by $1 = (2Dt)^{1/2}$, where D is the diffusion coefficient and t is time. To prevent aging of the photocells it was recommended that the optimal thickness of the n-layer be kept at 0.5 to 1 μ and the upper electrode have a small diffusion coefficient; aging was eliminated in CdSe or CdS by using elements of 0.5µ with Au of 0.1µ thickness for the upper electrode. For zero illumination the temperature dependence of the volt-ampere curves was determined for junctions of 99.99999% Se. The density of reverse current decreased with increase in temperature and attained saturation in the 353 to 413°K range. Activation energy (AE) was obtained from lnI vs 1/T plot since $I = \exp(-\Delta E/kT)$ and came out to 0.6 ev. The volt-ampere characteristics were also given for different amounts of illumination at 373°C where the current increased proportionally with illumination. These photodiodes were rated superior to standard selenium photoelements on the basis of sensitivity and response. Orig. art. has: 6 figures, 6 formulas.

SUB CODE: 11,09,20/

SUBM DATE: 10Mar65/

ORIG REF: 010/

009 OTH REF:

High purity SE

Card 2/2 5M

44.18

"APPROVED FOR RELEASE: 08/23/2000

CIA-RDP86-00513R000514410016-9

HAKHRAMOV, Idil' Bagadur; GASYMOV, S., red.

[Sorgo growing in Azerbaijan] Azerbaichanda sorgo bitkisinin becherilmesti. Baky, Azerbaichan SSR Elmler Akad. Neshriilaty 1963. 62 p. [In Azerbaijani] (MIRA 17:5)

GASYMOV, S. G., Cand Agric Sci (diss) -- "Optimum sowing times for post-harvest crops on the low irrigated regions of the Kuba-Khachmas zone of the Azerbaydzhan SSR". Baku, 1960. 18 pp (Acad Sci Turkmen SSR, Dept of Biol and Agric Sci), 150 copies (KL, No 14, 1960,134)

GASYMOV, S.G., kand.sel'skokhoz. nauk

Sowing pulse crops on stubble in the Kuba-Khachmas zone of Azerbaijan. Zemledelie 23 no.6:70-71 Je 161. (MIRA 14:6)

l. Azerbaydzhanskiy nauchno-issledovatel'skiy institut zemledeliya.

(Azerbaijan-Legumes)

ACC NR: AP(005531

SCURCE CODE: UR/0181/67/009/001/0166/0115

AUTHOR: Gurevich, L. E.; Gasymov, T. M.

ORG: Physicotechnical Institute im. A. F. Ioffe, AN SSSR, Leningrad (Fizikotekhnicheskiy institut AN SSSR); Institute of Physics, AN AzerbSSR, Baku (Institut fiziki AN AzerbSSR)

TITLE: Heating of phonons in semiconductors in a strong electric field, and its influence on the electric conductivity

SOURCE: Fizika tverdogo tela, v. 9, no. 1, 1967, 106-115

TOPIC TAGS: Germanium semiconductor, semiconductor conductivity, phonon interaction, electric field, electron temperature, [LECTRIC (DESCRIVITY)

ABSTRACT: The authors analyze the influence of phonon heating on the electric conductivity of n-type germanium with electron density ~10¹⁴ cm⁻³. A number of reasons are advanced why the authors believe that the results of V. V. Paranjape (Proc. Phys. Soc. v. 80, 171, 1963) and E. M. Conwell et al. (Phys. Rev. v. 135, A814, 1964) are not valid. It is shown that phonon heating is possible at low temperatures, when the phonon mean free path exceeds the crystal dimension. An important factor here is that the time necessary for the phonon to give up energy on the crystal boundaries is much larger than the quasimomentum transfer time. Cases of not too strong heating of electrons interacting only with long-wave subthermal phonons are considered, and also the case of strong heating of electrons emitting superthermal phonons. In the

Card 1/2

ACC NR: AP7005331

case of the subthermal phonons, the thermal phonons of the lattice provide a thermal reservoir, while in the case of the superthermal phonons there is no thermal reservoir. It is shown that in the latter case the electric conductivity can have a nonmonotonic variation when the field becomes stronger, namely a minimum followed by a maximum. Orig. art. has: 38 formulas.

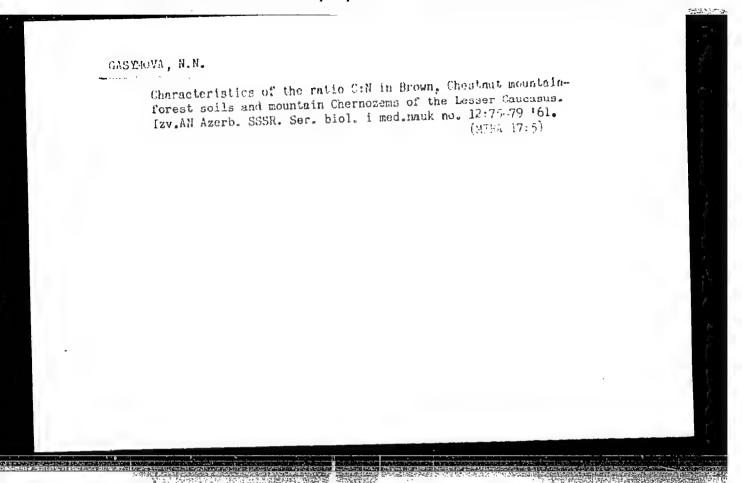
SUB CODE: 20/ SUBM DATE: 23May66/ ORIG REF: 004/ OTH REF: 005

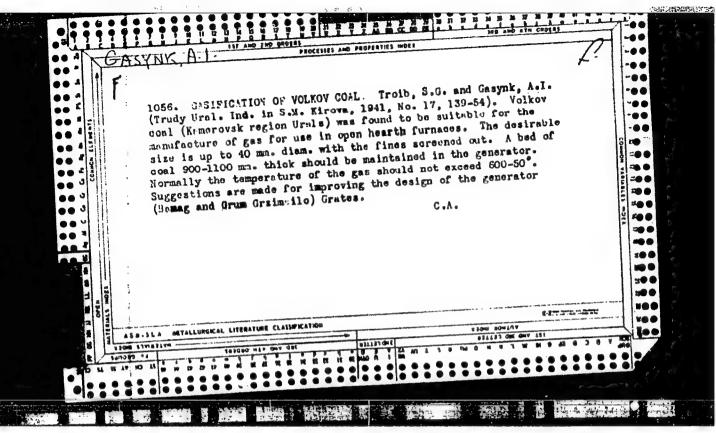
Card 2/2

GUNDOROVA, R.A., kand. med. nauk; GASYMOV, V.G., aspirant

Analysis of the outcome of mechanical eye injuries due to foreign bodies for a period of 8 years. Azerb. med. zhur. 42 no.8:55-62 Ag '65. (MIRA 18:11)

1. Is gosudarstvennogo nauchno-issledovatel'skogo instituta glaznykh bolezney imeni Gel'mgol'tsa (dir. - A.V. Roslavtsev) (rukovoditel' - starshiy nauchnyy sotrudnik, kand. med. nauk Ye.S. Vaynshteyn).





FEN'VESH, E.; GEMESHI, T.; NEMET, F.; SHANDOR, T.; GASYOROVSKI, L.; STARZHINSKI, A.

Semiautomatic measuring instrument for processing pictures obtained in the bubble chamber and the Wilson chamber. Prib. i tekh. eksp. 6 no.2:68-72 Mr-Ap *61. (MIRA 14:9)

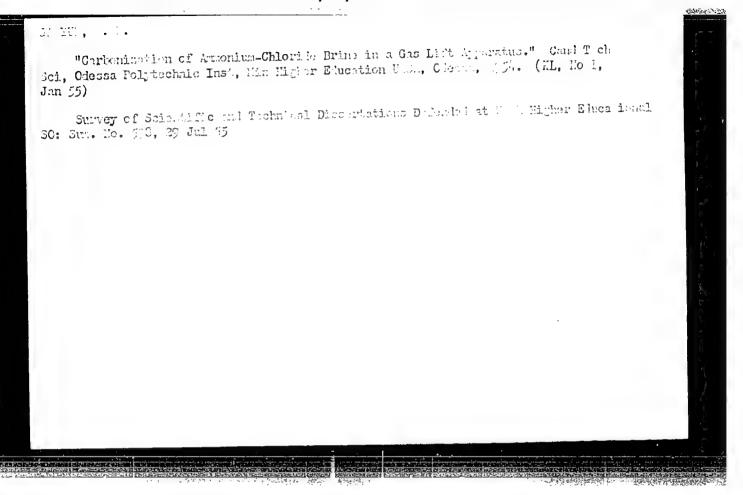
1. TSentral'nyy isledovatel'skiy institut fiziki, Budapesht (for Fen'vesh, Gemeshi, Memet, Shandor). 2. Institut yadernykh issledovaniy, Varshava (for Gasyorovski, Starzhinski).

(Photography, Particle track)

VOLKOV, Ye.V.; GASTUK, A.I.; MAGRACHEV, S.L.; SYROMYATNIKOV, N.I.

Characteristics of Otor'insk coal. Trudy Ural politekh. inst.
mo.76:35-40 '60.

(Khanty-Mansi National Area—Coal—Analysis)



GASYUK, G.N.; BOL'SHAKOV, A.G.; KORTHEV, A.V.; KRAYMY, P.Ya.

Mass transfer coefficient in liquid phase. Zhur. prikl. khim.
31 no.7:1019-1025 J1 *58. (MIRA 11:9)

1. Odesskiy politekhnicheskiy institut.
(Mass transfer)

GASYUK, G.N.; KRAYNIY, P.Ya.; BOL'SHAKOV, A.G.; KORTNEV, A.V. Effect of the partial pressure of influent carbon dioxide and

temperature on carbonation. Zhur.prikl.khim. 31 no.12:1787-1792 (MIRA 12:2)

D 158.

1. Odesskiy politekhnicheskiy institut. (Sodium carbonates) (Carbon dioxide) (Gases--Absorption)

"APPROVED FOR RELEASE: 08/23/2000

CIA-RDP86-00513R000514410016-9

POPOVSKIY, V.G.; GASYUK, G.N.; MATOV, B.M.

Treatment of grapes with ultrasonic waves before squeezing.
Kons. 1 ov. prom. 14 no.11:29-30 N '59. (MRA 13:2)

1. Moldavskiy nauchno-issledovatel'skiy institut pishchevoy promyshlennosti.

(Ultrasonic waves--Industrial application) (Grape juice)

SOV/80-59-1-15/44

AUTHORS:

Gasyuk, G.N., Bol'shakov, A.G., Kortnev, A.V. and Krayniy, P.W.

TITLE:

Coefficients of Mass Transfer in Caseous Phase (Koeffitsiyenty massoperedachi v gazovoy fame) Second Communication (So-

obshcheniye II)

PERIODICAL:

Zhurnal prikladnoy khimii, 1959, Ar 1, pp 95-99 (USSR)

ADSTRACT:

This investigation was performed for the purpose of calculating absorption processes in a was-lift apparatus for various gas - liquid systems. In a previous paper $\sqrt{Ref. 17}$ the authors presented the results of studying the dependence of mass transfer coefficient on the velocity of liquids and the depth of immersion in the liquid phase. The present paper furnishes analogous information for the gaseous phase, obtained on a special experimental installation for the system sulfur dioxide - air - water. The authors established a re= lationship between the mass transfer coefficient in the gaseous phase and the volumetric velocity of the gas and the depth of immersion. The treatment of the experimental data was carried out by Bol'shakov's method [Ref. 6] with the application of the theory of similarity. The generalized equation expressing the relation found looks as follows:

Card 1/2

Nu = 0.032 Re_ 9

Coefficients of Mass Transfer in Gaseous Phase

SOV/80-50-1-10/4.

where Eul is the diffusion criterion of the Eusselt type, he is keynolds criterion for the gas, Pr! is Prindtl's diffusion criterion for the gas, and h is indecision with An per cent. Wher are 2 graphs and C Seviet references.

Angue tamion:

Odesskip politekhnicheskiy institut (Odersa Polytechnic Tastitute)

GUENITTED:

May 8, 1957

Card 2/2

5(2) \$0\times 80-32-4-11/47

AUTHORS: Gasyuk, G.N., Bol'shakov, A.G., Kortnev, A.V., Krayniy, P.Ya.

TITLE: Dependence of the Process of Carbonization of Ammonia Brines in the Gas Lift Apparatus on Hydrodynamic Factors (Zavisimost'

protsessa karbonizatsii ammiachnykh rassolov v gazliftnom appa-

rate of gidrodinamicheskikh faktorov). Communication 2

(Soobshcheniye 2)

PERIODICAL: Zhurnal prikladnoy khimii, 1959, Vol 32, Nr 4, pp 770-777 (USSR)

ABSTRACT: The effect of the consumption of liquid and gas on the carboni-

zation of ammonia brines is investigated. The gas consumption varied from $5,650~\text{m}^3/\text{m}^2$. hour to $5,800~\text{m}^3/\text{m}^2$. hour, the concentration of the entering carbon dioxide from 36 to 38%, the consumption of liquid from 42 to 397 m $^3/\text{m}^2$. hour, the depth of immersion from 7 to 30%. It is shown that the increase of the liquid consumption raises the general absorption coefficient only slightly: a 9.5-fold increase of the former causes only

a 1.5-fold increase of the latter. Figure 3 shows the dependence of the absorption coefficient on liquid consumption in

card 1/2 brines with various ammonia contents and Figure 4 for brines

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SOV/80-32-4-11/47

Dependence of the Process of Carbonization of Ammonia Brines in the Gas Lift Apparatus on Hydrodynamic Factors. Communication 2

> with various degrees of carbonization. The dependence of the degree of carbonization on the gas consumption was studied at a temperature of 30°C, a liquid consumption of 183 m³/m². hour, a carbon dioxide concentration of 37-38%. Gas consumption varied from 2,720 to 12,510 m³/m². hour. The immersion depth varied from 10 to 25%.

There are 11 graphs and 2 Soviet references.

SUBMITTED:

October 8, 1957

Card 2/2

GASYUK, G.H.: MATOV, B.H. Treating grapes with high-frequency electric current before pressing. Kons.i ov.prom. 15 no.1:9-11 Ja '60.

(MIRA 13:5)

1. Moldavskiy nauchno-issledovatel'skiy institut pishchevoy promyahlennosti. (Grapes)

CIA-RDP86-00513R000514410016-9" APPROVED FOR RELEASE: 08/23/2000

GASYUK, G. N.; MATOV, B. M.

Treatment of grapes with increased frequency currents.

Trudy MNIIPP 1:45-48 '61. (MIRA 16:1)

(Grape juice) (Electrolysis)

Clarification of grape juice by the electric current. Kons.i ov.prom. 15 no.7:3-6 J1 '60. (MEA 13:6)

1. Moldavskiy nauchno-issledovatel'skiy institut pishchevoy promyshlennosti.

(Grape juice)

GASYUK, G.N.; KORTNEY, A.V.

Thorough preliminary carbonization in gas-lift units in the soda production. Khim.prom. no.5:399-401 J1-Ag '60.
(MIRA 13:9)

1. Odesskiy politekhnicheskiy institut.
(Soda industry--Equipment and supplies) (Carbon dioxide)

POPOVSKIY, V.C.; GASYUK, G.N.; MATOV, B.M.; LEVINA, M.V.

Effect of ultrasonic waves on the yield and color of grape juice.

Kons.i ov.prom. 16 no.1:4-6 Ja '61. (MIRA 13:12)

1. Moldavskiy nauchno-issledovatel skiy institut pishchevoy promyshlennosti.

(Grape juice)

(Ultrasonic waves--Industrial applications)

ZAPOL'SKAYA, L.M.; BOL'SHAKOV, A.G.; GASYUK, G.N.

Dependence of carbonic acid chemisorption by water-ammonia solutions on the concentration of ammonia in solution and the

extent of carbonization. Zhur.prikl.khim. 34 no.9:2096-2099 S '61. (MIRA 14:9)

1. Odesskiy politekhnicheskiy institut.
(Carbonic acid) (Sorption) (Ammonia)

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CIA-RDP86-00513R000514410016-9

ZAPOL'SKAYA, L.M.; BOL'SHAKOV, A.G.; GASYUK, G.N.

Chemisorption of carbonic acid by water-ammonia solutions as a function of hydrodynamic factors and salt admixtures. Zhur.prikl. khim. 34 no.10:2183-2187 0 '61. (MIRA 14:11)

1. Odesskiy politekhnicheskiy institut. (Carbonic acid) (Sorption) (Ammonia)

CASYUK, G. N.; MATOV, B. M.

New method of removing suspended particles from fruit and berry juices. Trudy MNIIPP 1:63-73 '61. (MIRA 16:1)

(Fruit juices) (Electrolysis)

GASYUK, G. N.; POPOVSKIY, V. G.; DUL'NEVA, I. P.; LEVINA, M. V.

Speeding the crystallization of tartar in the treatment of grape juice with ultrasonic waves in tanks. Trudy MNIIPP 1: 83-87 '61. (MIRA 16:1)

(Grape juice)
(Ultrasonic waves—Industrial applications)

GASTUK, G. N.; DUL'NEVA, I. P.; POFOVSKIY, V. G.

Effect of ultrasomic waves on the rate of tartar precipitation from grape juice. Trudy MNIIFP 1:75-82 '61.

(Wira 16:1)

(Ultrasonic waves—Industrial applications)

(Grape juice)

ZAPOL'SKAYA, L.M.; BOL'SHAKOV, A.G.; GASYUK, G.N.

Relation between chemisorption and the concentration and temperature of carbon dioxide and the effect of ultrasonic waves. Zhur. prikl. khim. 34 no.5:1040-1046 My '61.

(MIRA 16:8)

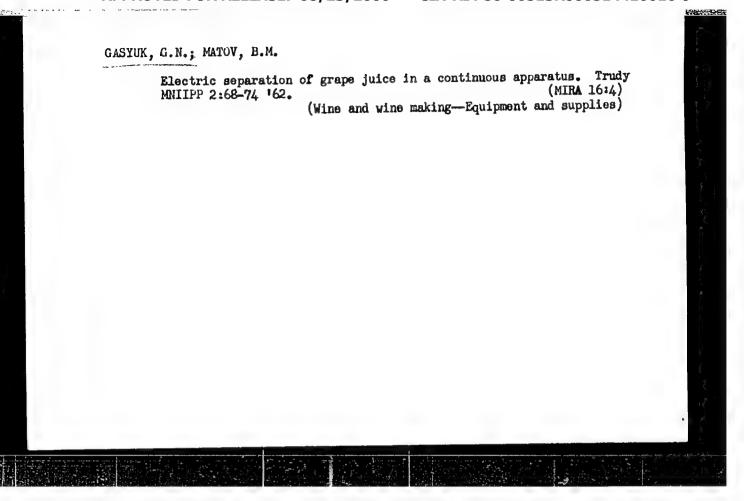
1. Odesskiy politekhnicheskiy institut.
(Carbon dioxide) (Chemisorption)
(Ultrasonic waves—Industrial applications)

GASYUK, G.N.; DUL'NEVA, I.P.; LEVINA, M.V.

Manufacture of clarified grape juice by means of a simplified technology with the application of ultrasonic waves. Trudy MMITPP 2:56-66 '62.

(MIRA 16:4)

(Grape juice) (Ultrasonic waves—Industrial application)



GASYUK, G.N.; TSVETKOVA, L.M.; Prinimali uchastive: SHVETS, A.T.; LAGUNOVA, G.A.

Effect of ultrasonic waves on the microflora in the process of grape
juice production. Trudy MNIIPP 2:75-80 '62. (MIRA 16:4)
(Ultrasonic waves—Industrial applications)
(Wine and wine making—Microbiology)

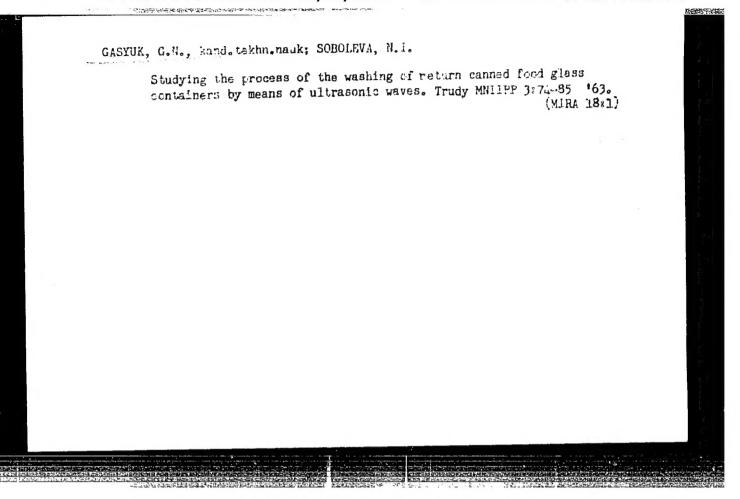
GASYUK, G.N.; TSVETKOVA, L.M.

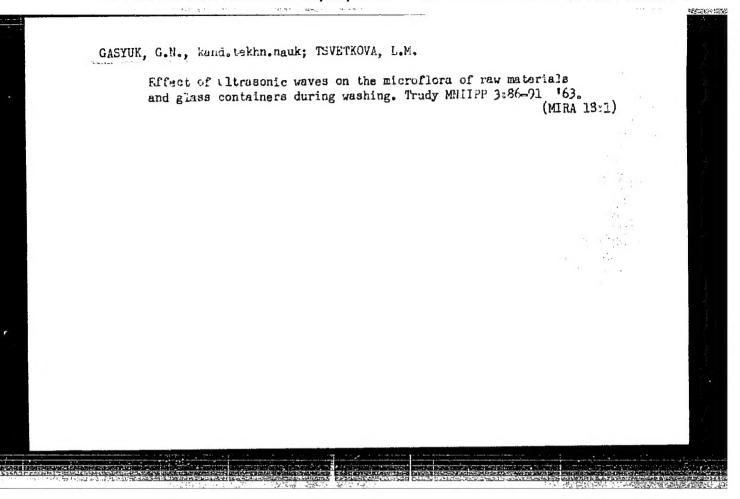
Effect of ultrasonic waves on the microflora in the manufacture of grape juice. Kons.i ov.prom. 17 no.12:12-15 D '62. (MIRA 15:12)

1. Moldavskiy nauchno-issledovatel skiy institut pishchevoy promyshlennosti.
(Ultrasonic waves-Physiological effect) (Grape juice-Microbiology)

GASYUK, G.N.; DUL'NEVA, I.P.; LEVINA, M.V.

Manufacture of clarified grape juice by means of a simplified technology with the application of ultrasonic waves. Trudy MNIPP 2456-66 '62. (MIRA 16:4) (Grape juice) (Ultrasonic waves--Industrial application)





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CIA-RDP86-00513R000514410016-9

GASYUK, G.N.; LEVINA, M.V.; SOBOLEVA, N.J.

Accelerating the processes of potassium bitartrate crystallization and wine clarification by means of ultrasonic waves. Trudy MNIPP (MIRA 18:1) 42:52.31 164.

